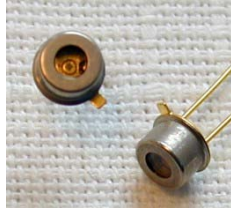


AG32S**UVB sensitive AlGaN based UV photodiode A = 0,076 mm²****General Features****Properties of the AG32S UV photodiode**

- UVB sensitive photodiode
- Active Area A = 0,076 mm²
- TO18 metal housing
- 10mW/cm² peak radiation results a current of approx. 700 nA

About the material (Aluminium)Gallium Nitride (Al)GaN

(Al)GaN is a new semiconductor material for visible blind UV photodiodes. By modification of the Al – to - Ga stoichiometry it is possible to produce photodiodes with different spectral behaviour. This allows to offer Photodiodes sensible for broad band UV (UVA+UVB+UVC), for UVB-only and for UVC only without using a filter.

Specifications

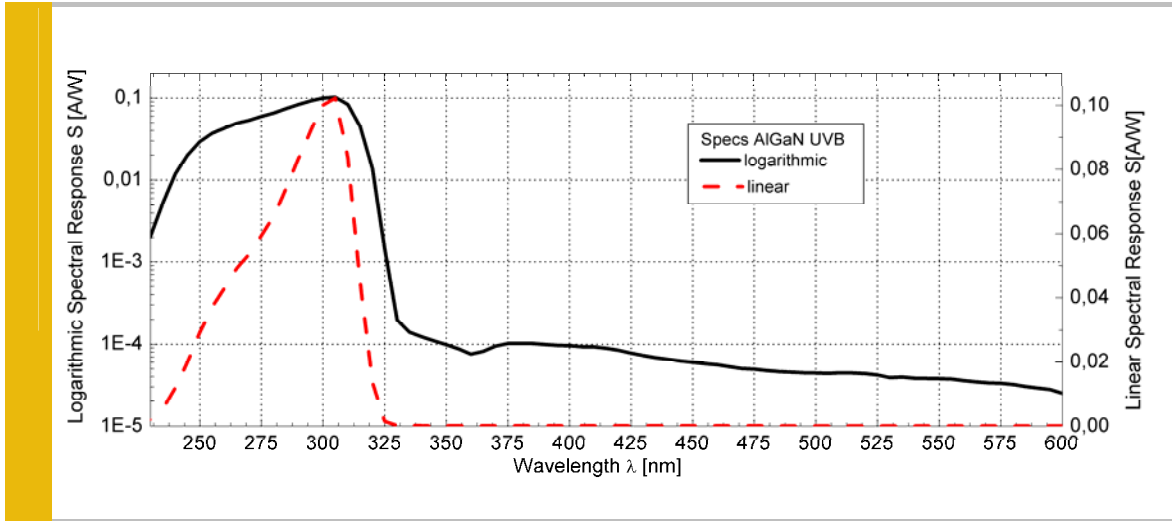
Parameter	Symbol	Value	Unit
Maximum Ratings			
Operating Temperature Range	T_{opt}	-25 ... +70	°C
Storage Temperature Range	T_{stor}	0 ... +100	°C
Soldering Temperature (3s)	T_{sold}	260	°C
Reverse voltage	V_{Rmax}	5	V
General Characteristics (T=25°C)			
Active Area	A	0,076	mm ²
Dark current (1V reverse bias)	I_d	100	fA
Capacitance	C	24	pF
Short circuit (10mW/cm ² at peak)	I_0	700	nA
Temperature coefficient	Tc	<-0,3	%/K
Spectral Characteristics (T=25°C)			
Max. spectral sensitivity	S_{max}	0,130	AW ⁻¹
Wavelength of max. spectral sens.	λ_{max}	310	nm
Sensitivity range (S=0,1*S _{max})	-	240 ... 320	nm
Visible blindness (S _{max} / S _{>400nm})	VB	10 ³	-

AG32S

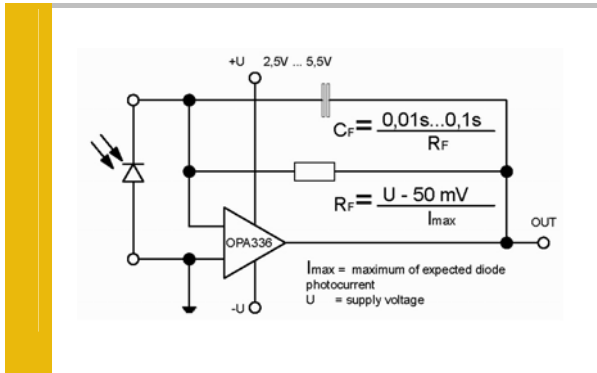
UVB sensitive AlGaN based UV photodiode $A = 0,076 \text{ mm}^2$



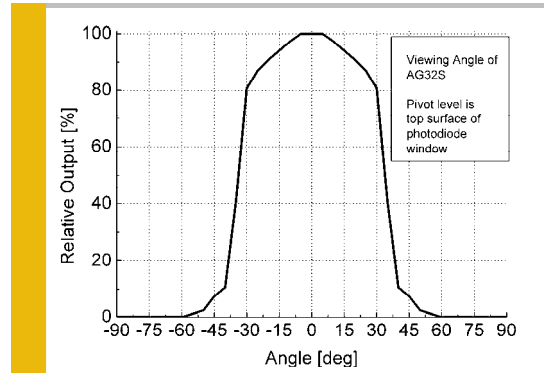
Spectral Response



Circuit



Viewing Angle



Drawing

